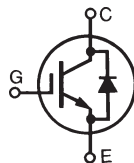


High Voltage, High Gain BiMOSFET™

IXBK55N300 IXBX55N300

Monolithic Bipolar MOS Transistor



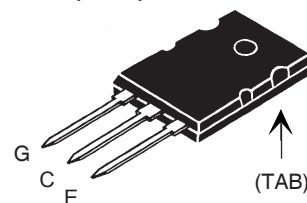
$$V_{CES} = 3000V$$

$$I_{C110} = 55A$$

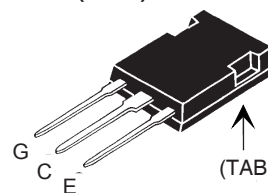
$$V_{CE(sat)} \leq 3.2V$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	3000	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	3000	V
V_{GES}	Continuous	± 25	V
V_{GEM}	Transient	± 35	V
I_{C25}	$T_C = 25^\circ C$ (Chip Capability)	130	A
I_{LRMS}	$T_C = 25^\circ C$ (Lead RMS Limit)	120	A
I_{C110}	$T_C = 110^\circ C$	55	A
I_{CM}	$T_C = 25^\circ C$, 1ms	430	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 2\Omega$ Clamped Inductive Load	$I_{CM} = 110$ @ $0.8 \cdot V_{CES}$	A
T_{SC} (SCSOA)	$V_{GE} = 15V$, $T_J = 125^\circ C$, $R_G = 10\Omega$, $V_{CE} = 1250V$, Non-Repetitive	10	μs
P_C	$T_C = 25^\circ C$	625	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L T_{SOLD}	Maximum Lead Temperature for Soldering 1.6 mm (0.062 in.) from Case for 10	300 260	$^\circ C$ $^\circ C$
M_d F_C	Mounting Torque (TO-264) Mounting Force (PLUS247)	1.13/10 20..120/4.5..27	Nm/lb.in. N/lb.
Weight	TO-264 PLUS247	10 6	g g

TO-264 (IXBK)



PLUS247™ (IXBX)



G = Gate C = Collector
E = Emitter TAB = Collector

Features

- High Blocking Voltage
- International Standard Packages
- Low Conduction Losses
- High Current Handling Capability
- MOS Gate Turn-On
- Drive Simplicity

Applications

- Uninterruptible Power Supplies (UPS)
- Switched-Mode and Resonant-Mode Power Supplies
- Capacitor Discharge Circuits
- Laser Generators

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 1mA$, $V_{GE} = 0V$	3000		V
$V_{GE(th)}$	$I_C = 4mA$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ C$			50 μA 3 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 25V$			± 200 nA
$V_{CE(sat)}$	$I_C = 55A$, $V_{GE} = 15V$, Note 1 $T_J = 125^\circ C$	2.7 3.3	3.2	V V

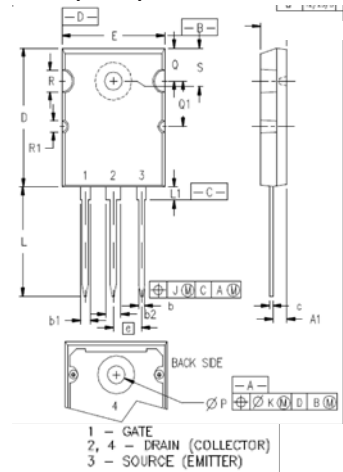
Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

		Min.	Typ.	Max.	
g_{fs}	$I_C = 55\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	32	50		S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		7300		pF
C_{oes}			275		pF
C_{res}			83		pF
Q_g	$I_C = 55\text{A}, V_{GE} = 15\text{V}, V_{CE} = 1000\text{V}$		335		nC
Q_{ge}			47		nC
Q_{gc}			130		nC
$t_{d(on)}$	Resistive Switching Times, $T_J = 25^\circ\text{C}$ $I_C = 110\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 1250\text{V}, R_G = 2\Omega$		54		ns
t_r			307		ns
$t_{d(off)}$			230		ns
t_f			268		ns
$t_{d(on)}$	Resistive Switching Times, $T_J = 125^\circ\text{C}$ $I_C = 110\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 1250\text{V}, R_G = 2\Omega$		52		ns
t_r			585		ns
$t_{d(off)}$			215		ns
t_f			260		ns
R_{thJC}				0.20	$^\circ\text{C/W}$
R_{thCS}		0.15			$^\circ\text{C/W}$

TO-264 (IXBK) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

Reverse Diode

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

		Min.	Typ.	Max	
V_F	$I_F = 55\text{A}, V_{GE} = 0\text{V}, \text{Note 1}$			2.5	V
t_{rr}	$I_F = 28\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}$		1.9		μs
I_{RM}		$V_R = 100\text{V}, V_{GE} = 0\text{V}$		54	

Note

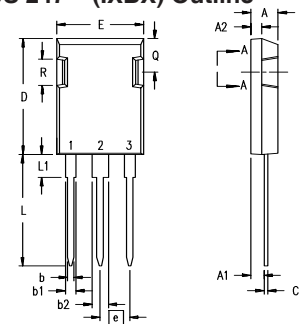
1: Pulse Test, $t \leq 300\mu\text{s}$, Duty Cycle, $d \leq 2\%$.

Additional provisions for lead-to-lead isolation are required at $V_{CE} > 1200\text{V}$.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

PLUS 247™ (IXBX) Outline



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338 B2
by one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

Fig. 1. Output Characteristics @ 25°C

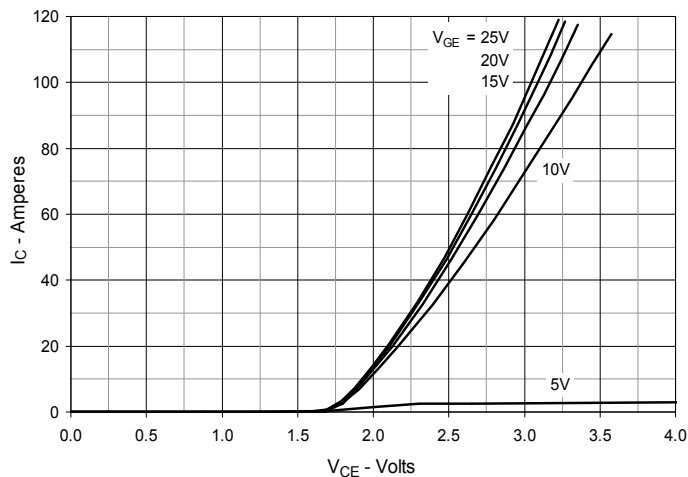


Fig. 2. Extended Output Characteristics @ 25°C

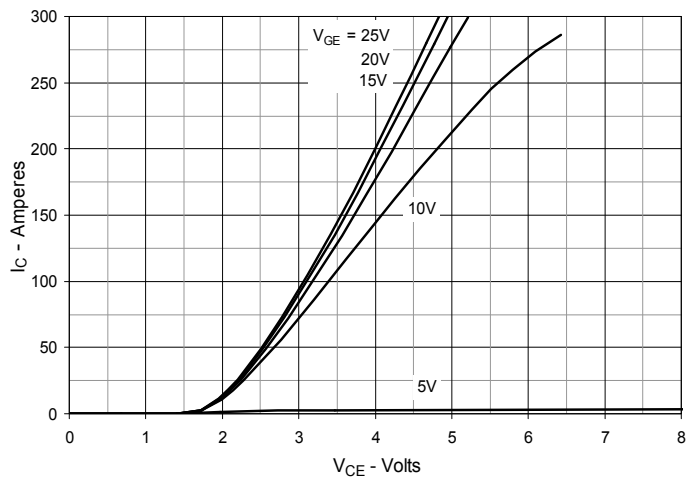


Fig. 3. Output Characteristics @ 125°C

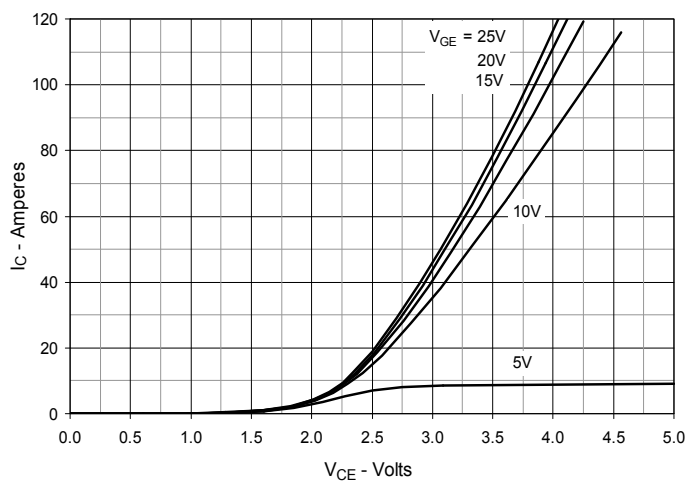


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

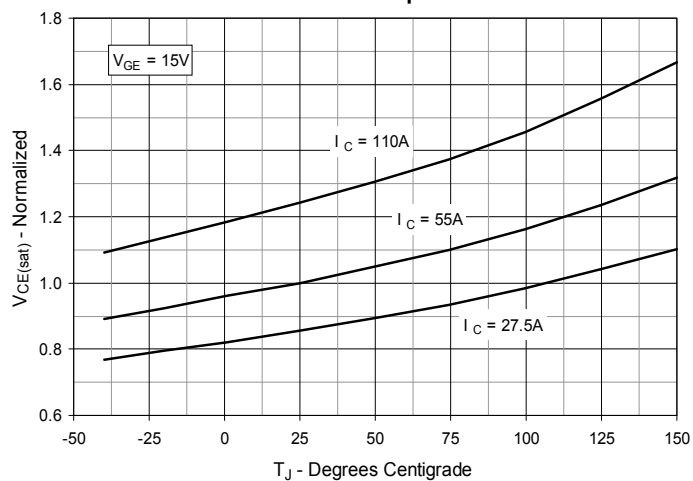


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

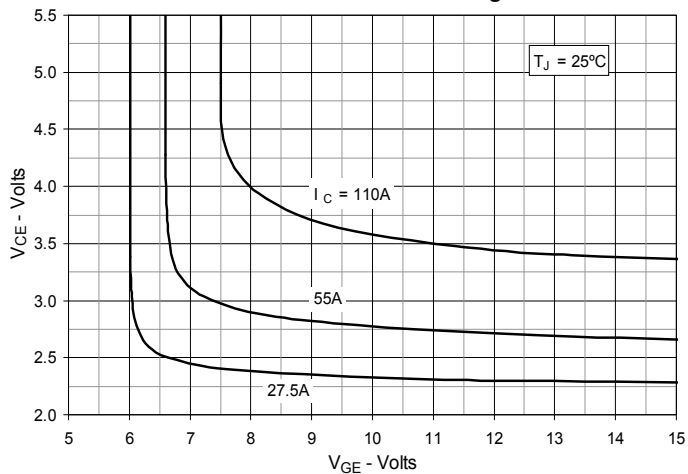


Fig. 6. Input Admittance

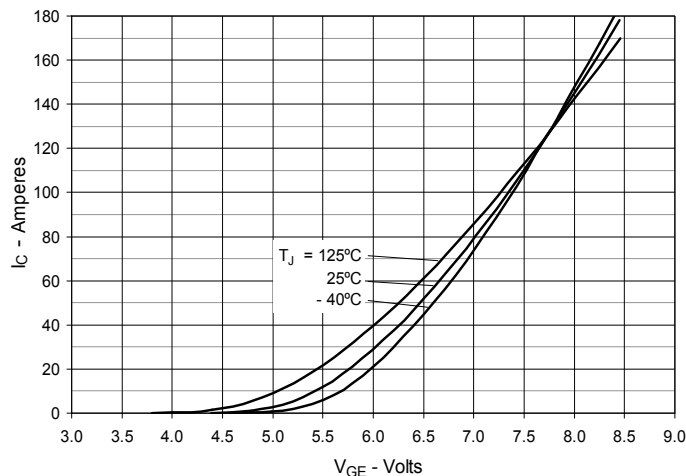
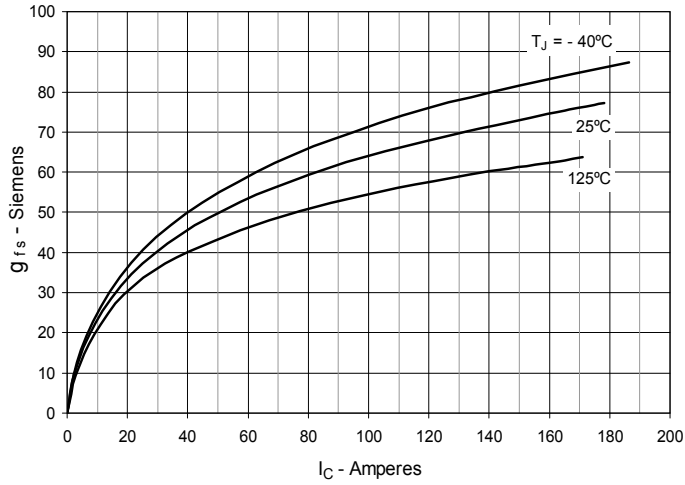
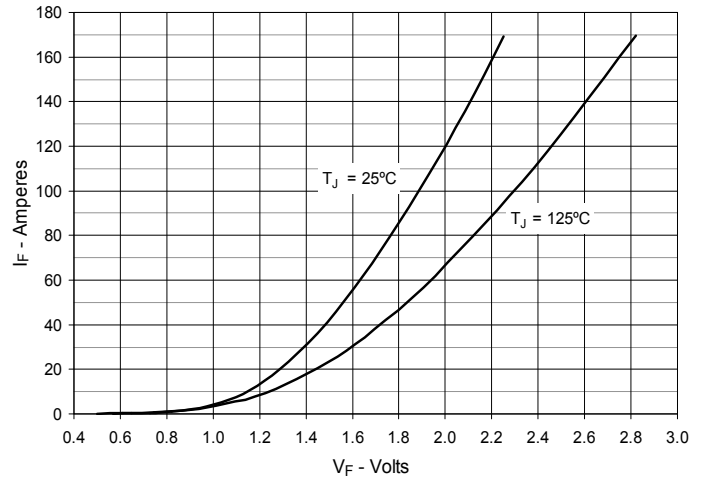
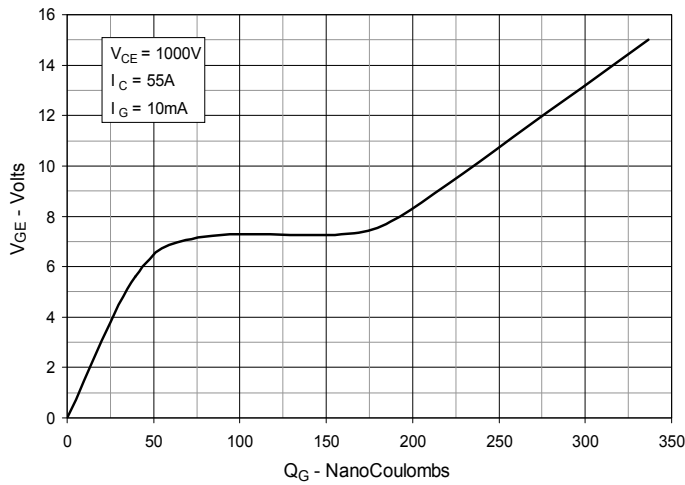
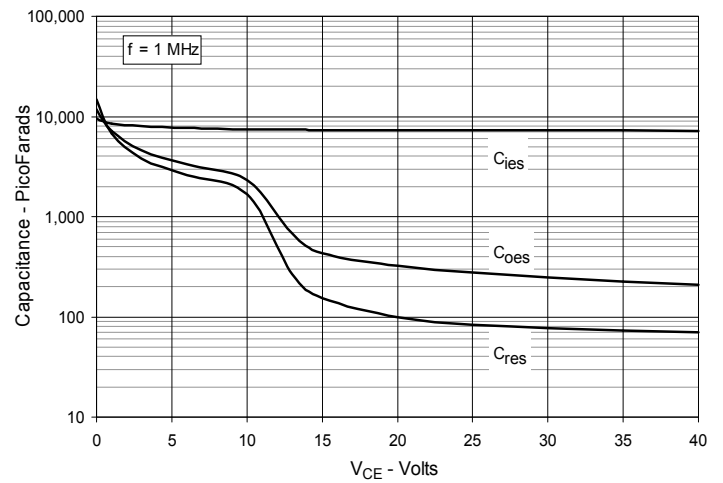
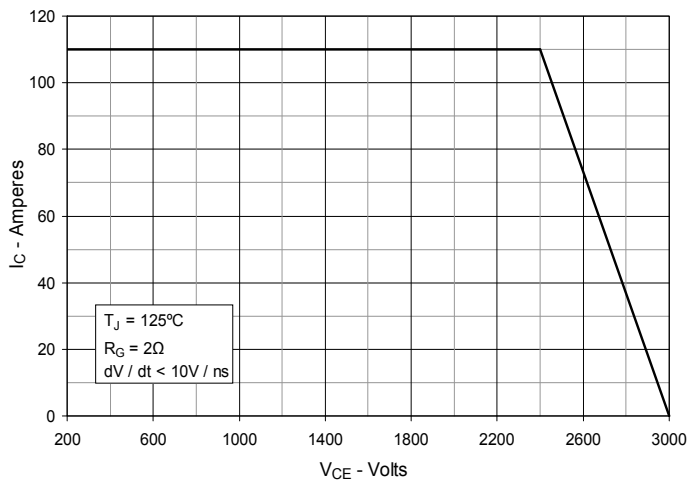
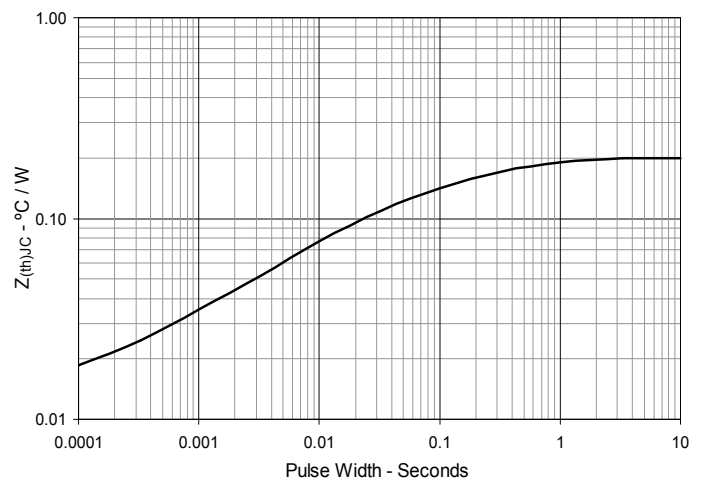
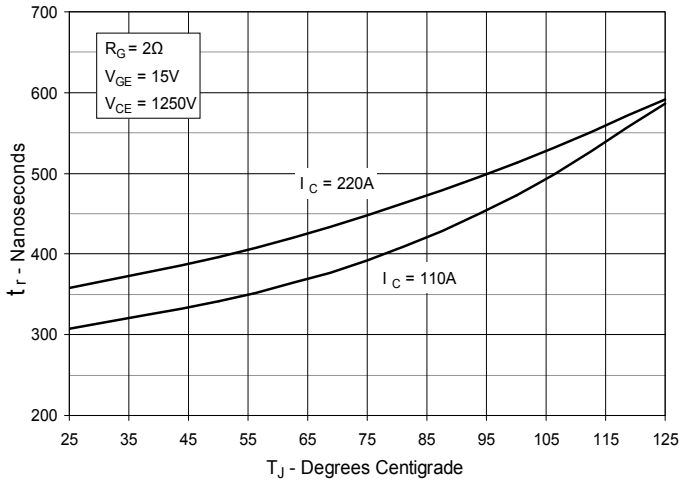
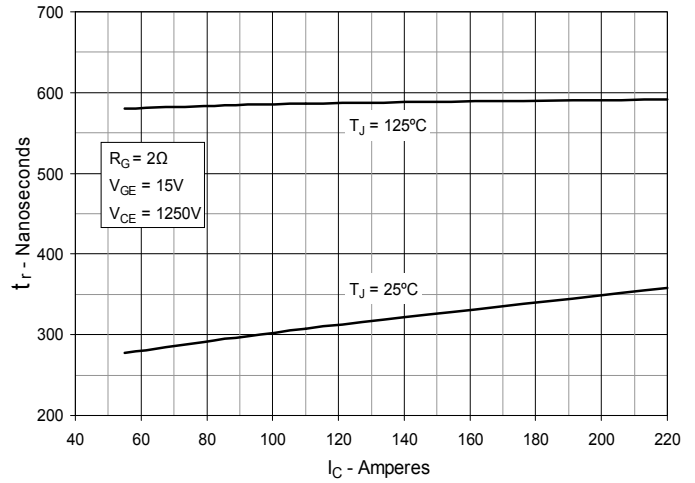


Fig. 7. Transconductance

Fig. 8. Forward Voltage Drop of Intrinsic Diode

Fig. 9. Gate Charge

Fig. 10. Capacitance

Fig. 11. Reverse-Bias Safe Operating Area

Fig. 12. Maximum Transient Thermal Impedance


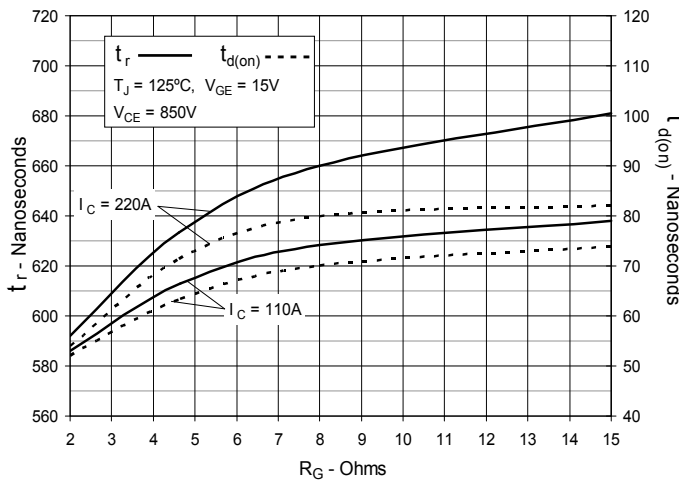
**Fig. 13. Resistive Turn-on
Rise Time vs. Junction Temperature**



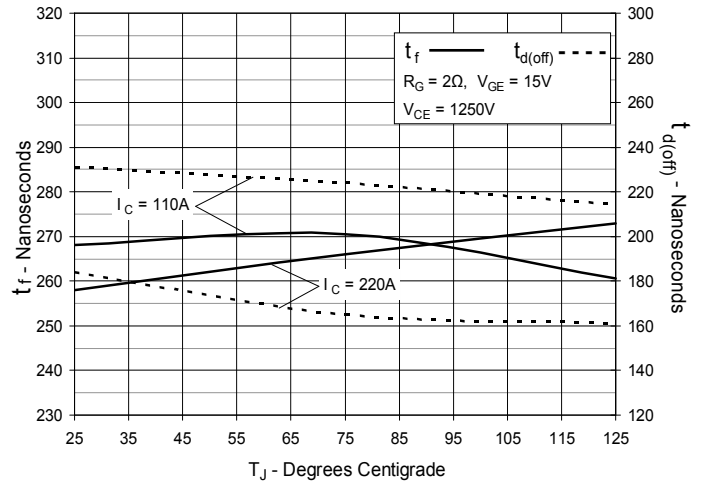
**Fig. 14. Resistive Turn-on
Rise Time vs. Collector Current**



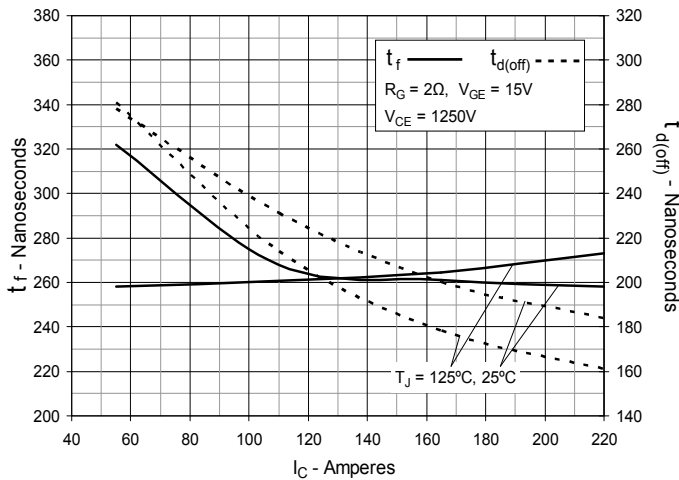
**Fig. 15. Resistive Turn-on
Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off
Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off
Switching Times vs. Collector Current**



**Fig. 18. Resistive Turn-off
Switching Times vs. Gate Resistance**

